

MMBT3904M

MMBT3904M NPN General Purpose Transistor

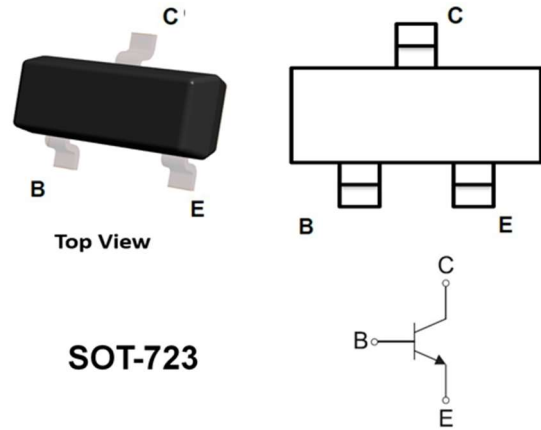
General description

- NPN General Purpose Transistor

FEATURES

- SOT-723 General Purpose Transistors.
- V_{CEO} 40V
- I_c 200mA
- P_C 100mW
- Complementary to MMBT3906M
- Small Outline Surface Mount Package.
- RoHS Compliant / Green EMC.

Type	MMBT3904M
Marking	1N



SOT-723

Absolute Maximum Ratings(T_a=25°C)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current -Continuous	I _c	0.2	A
Power Dissipation	P _C	0.1	W
Thermal Resistance from Junction to Ambient	R _{θJA}	1250	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~+150	°C

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ELECTRICAL CHARACTERISTICS @ 25°C Unless Otherwise Specified

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6			V
Collector cut-off current	I_{CEX}	$V_{CE}=30V, V_{EB(off)}=3V$			50	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			100	nA
DC current gain	h_{FE}	$V_{CE}=1V, I_C=0\text{ mA}$	40			
		$V_{CE}=1V, I_C=1mA$	70			
		$V_{CE}=1V, I_C=10mA$	100		300	
		$V_{CE}=1V, I_C=50mA$	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$			0.2	V
		$I_C=50mA, I_B=5mA$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10mA, I_B=1mA$	0.65		0.85	V
		$I_C=50mA, I_B=5mA$			0.95	V
Transition frequency	f_T	$V_{CE}=20V, I_C=10mA, f=100MHz$	300			MHz
Output capacitance	C_{ob}	$V_{CB}=5V, I_E=0, f=1MHz$			4	pF
Input capacitance	C_{ib}	$V_{EB}=0.5V, I_C=0, f=1MHz$			8	pF
Noise figure	NF	$V_{CE}=5V, I_C=0.1mA, f=1MHz, R_S=1k\Omega$			5	dB

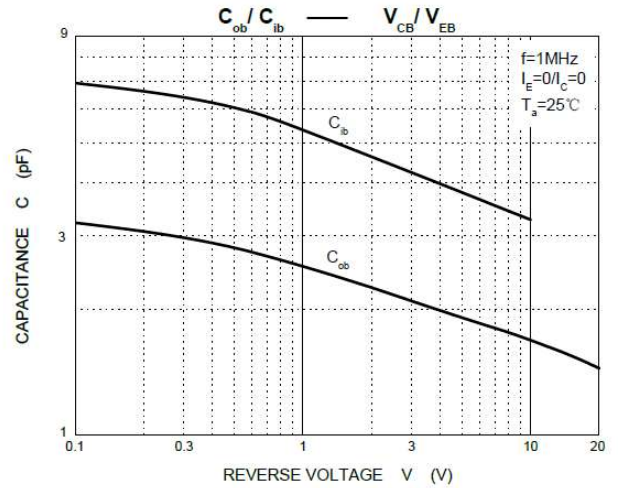
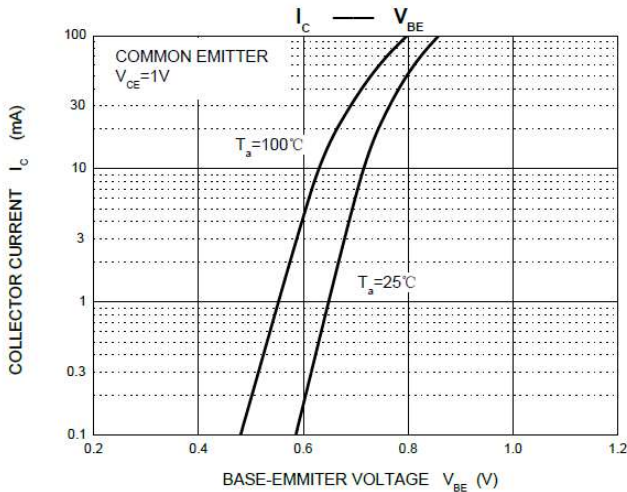
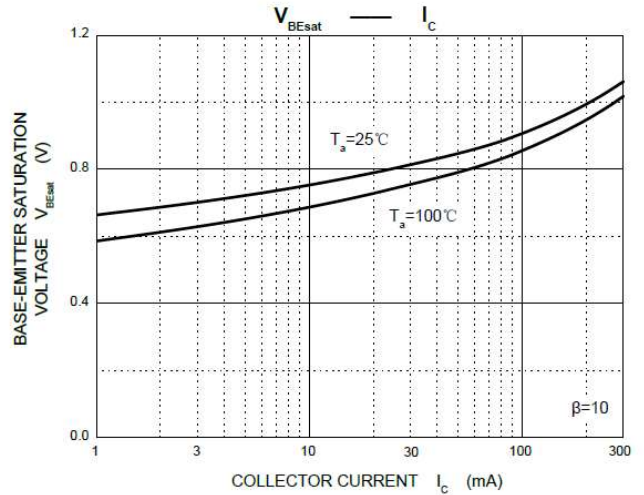
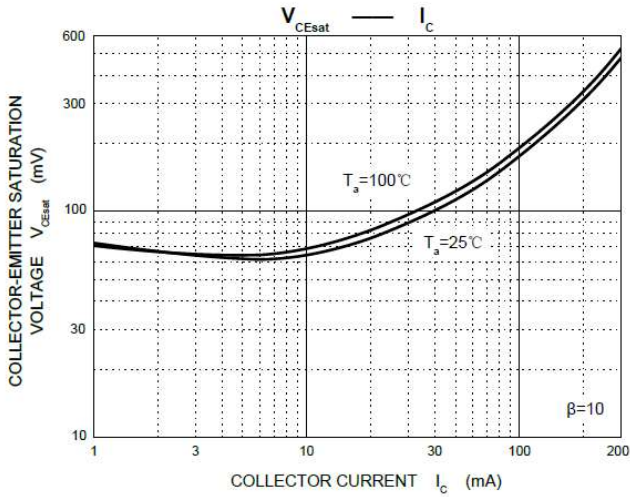
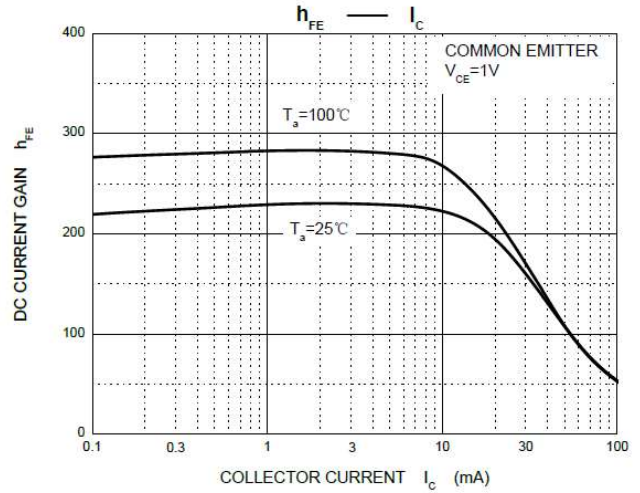
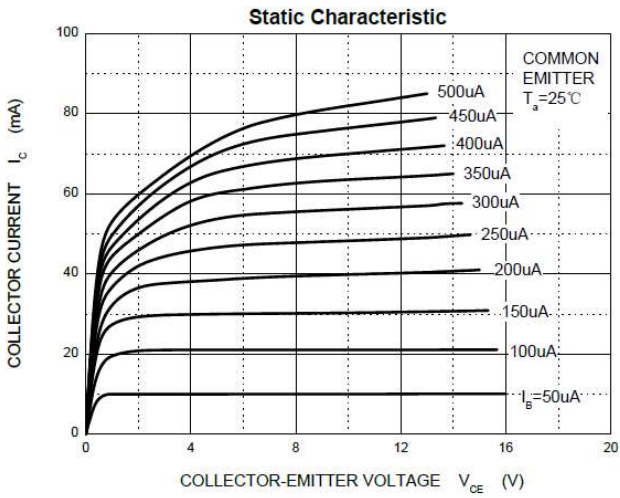
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Parameter	Symbol	Conditions	Min	Typ	Max	Units
Delay time	t_d	$V_{CC}=3V, V_{BE(off)}=-0.5V,$ $I_C=10mA, I_{B1}=1mA$			35	ns
Rise time	t_r				25	ns
Storage time	t_s	$V_{CC}=3V, I_C=10mA, I_{B1}=I_{B2}=1mA$			200	ns
Fall time	t_f				50	ns

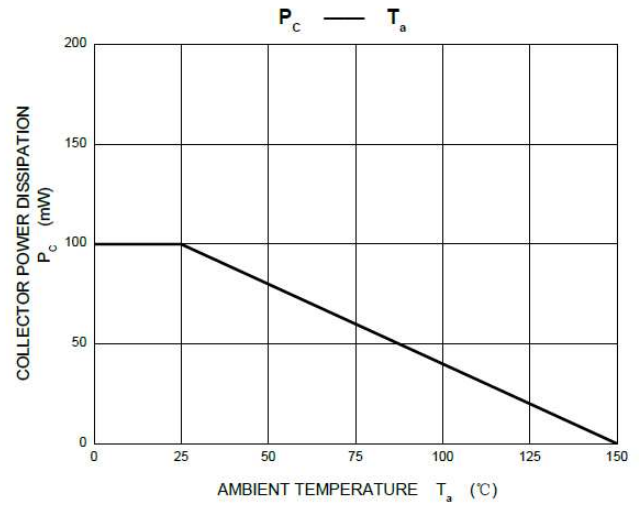
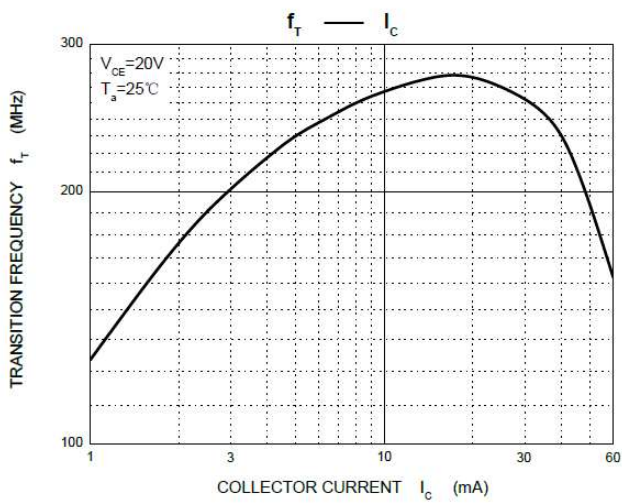
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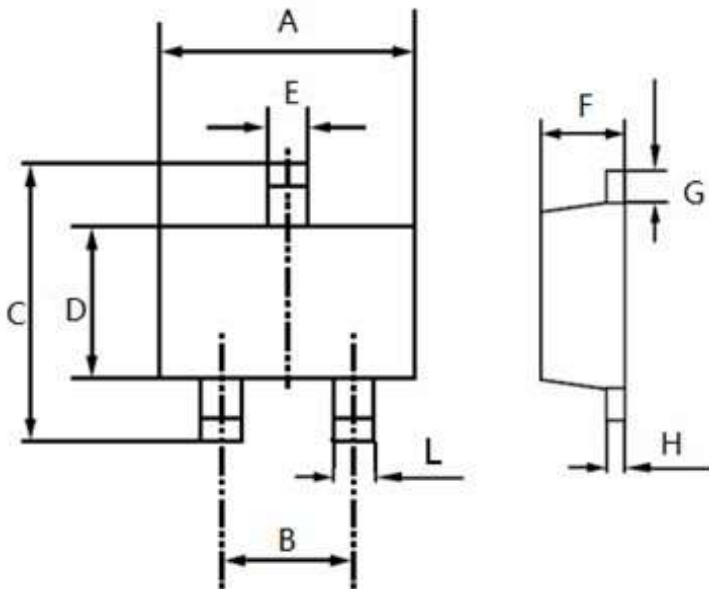
TYPICAL CHARACTERISTIC



MMBT3904M



PACKAGE DIMENSIONS



Symbol	Dimensions In Millimeters	
	Min	Max
A	1.100	1.300
B	0.8typ	
C	1.100	1.300
D	0.700	0.900
E	0.200	0.300
F	0.400	0.500
G	0.150	0.250
H	0.060	0.160
L	0.150	0.250

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